

PC3Q62

*1-channel package type is also available. (model No. **PC3H2 Series**)

Mini-flat Half Pitch 4-channel Package High CMR Photocoupler



■ Description

PC3Q62 contains a IRED optically coupled to a phototransistor.

It is packaged in a 4 channel Mini-flat, Half pitch type.

Input-output isolation voltage(rms) is 2.5kV.

Collector-emitter voltage is $80V^{(*)}$, CTR is 20% to 400% at input current of 1mA and CMR is MIN. $10kV/\mu s$.

■ Features

- 4 channel Mini-flat Half pitch package (Lead pitch : 1.27mm)
- 2. Double transfer mold package (Ideal for Flow Soldering)
- 3. High collector-emitter voltage (V_{CEO}: 80V^(*))
- 4. High noise immunity due to high common mode rejection voltage (CMR : MIN. 10kV/μs)
- 5. Isolation voltage between input and output ($V_{iso(rms)}$: 2.5kV)
 - (*) Up to Date code "P9" (September 2002) V_{CEO}: 35V. From the production Date code "J5" (May 1997) to "P9" (September 2002), however the products were screened by BV_{CEO}≥70V.

■ Agency approvals/Compliance

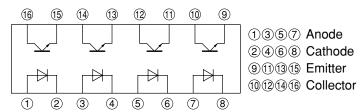
- 1. Recognized by UL1577 (Double protection isolation), file No. E64380 (as model No. **PC3Q62**)
- 2. Package resin: UL flammability grade (94V-0)

■ Applications

1. Programmable controllers

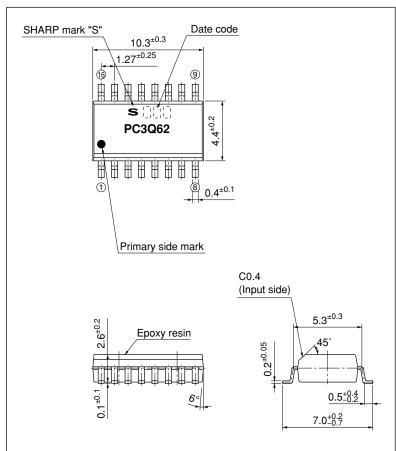


■ Internal Connection Diagram



■ Outline Dimensions





Product mass: approx. 0.3g



Date code (3 digit)

	1st o	digit		2nd digit		3rd digit		
Year of production				Month of production		Week of production		
A.D.	Mark	A.D	Mark	Month	Mark	Week	Mark	
1990	A	2002	P	January	1	1st	1	
1991	В	2003	R	February	2	2nd	2	
1992	С	2004	S	March	3	3rd	3	
1993	D	2005	T	April	4	4th	4	
1994	Е	2006	U	May	5	5, 6th	5	
1995	F	2007	V	June	6			
1996	Н	2008	W	July	7			
1997	J	2009	X	August	8			
1998	K	2010	A	September	9			
1999	L	2011	В	October	0			
2000	M	2012	С	November	N			
2001	N	•	:	December	D			

repeats in a 20 year cycle

Country of origin Japan



■ Absolute Maximum Ratings $(T_0=25^{\circ}C)$

			(1_a-25C)		
	Parameter	Symbol	Rating	Unit	
	Forward current	I_F	50	mA	
Input	*1 Peak forward current	I_{FM}	1	A	
Inf	Reverse voltage	V_R	6	V	
	Power dissipation	P	70	mW	
	Collector-emitter voltage	V_{CEO}	*4 80	V	
put	Emitter-collector voltage	V _{ECO}	6	V	
Output	Collector current	I_{C}	50	mA	
	Collector power dissipation	P _C	150	mW	
	Total power dissipation	P _{tot}	170	mW	
(Operating temperature	Topr	-30 to +100	°C	
- 5	Storage temperature	T_{stg}	-40 to +125	°C	
*2]	Isolation voltage	V _{iso (rms)}	2.5	kV	
*3 (Soldering temperature	T_{sol}	260	°C	

■ Electro-optical Characteristics

 $(T_3=25^{\circ}C)$

								$(T_a=25 C)$
Parameter			Symbol	Conditions	MIN.	TYP.	MAX.	Unit
	Forward voltage		V_F	$I_F=20mA$	_	1.2	1.4	V
Input	Reverse current		I_R	$V_R=4V$	_	_	10	μΑ
	Terminal capacitance		C_t	V=0, f=1kHz		30	250	pF
	Collector dark current		I_{CEO}	$V_{CE} = 50V, I_{F} = 0$	_	_	100	nA
Output	Collector-emitter breakdown voltage		BV_{CEO}	$I_{C}=0.1 \text{mA}, I_{F}=0$	*5 80	_	_	V
	Emitter-collector breakdown voltage		BV_{ECO}	$I_{E}=10\mu A, I_{F}=0$	6	_	_	V
	Collector current		I_{C}	$I_F=1$ mA, $V_{CE}=5$ V	0.2	_	4.0	mA
	Collector-emitter saturation voltage		V _{CE (sat)}	$I_F=20mA$, $I_C=1mA$	_	0.1	0.2	V
	Isolation resistance		$R_{\rm ISO}$	DC500V, 40 to 60%RH	5×10 ¹⁰	1×10 ¹¹	_	Ω
Transfer	Floating capacitance		C_{f}	V=0, f=1MHz	_	0.6	1.0	pF
charac- teristics	Response time	Rise time	t _r	V 2V I 2 A D 1000	_	4	18	μs
		Fall time	$t_{\rm f}$	$V_{CE}=2V$, $I_{C}=2mA$, $R_{L}=100\Omega$	_	3	18	μs
	Common mode rejection voltage		CMR	T_a =25°C, R_L =470 Ω , V_{CM} =1.5kV(peak) I_F =0, V_{CC} =9V, V_{np} =100mV	10	-	_	kV/μs

^{*5} From the production Date code "J5" (May 1997) to "P9" (September 2002), however the products were screened by BV_{CEO}≥70V.

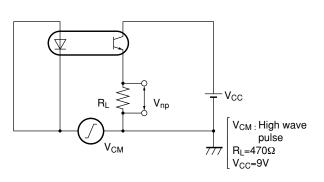
^{*1} Pulse width≤100µs, Duty ratio : 0.001 *2 40 to 60%RH, AC for 1 minute, f = 60Hz

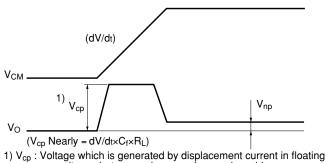
^{*3} For 10s

^{*4} Up to Date code "P9" (September 2002) V_{CEO}: 35V.



Fig.1 Test Circuit for Common Mode Rejection Voltage





capacitance between primary and secondary side.

Fig.2 Forward Current vs. Ambient **Temperature**

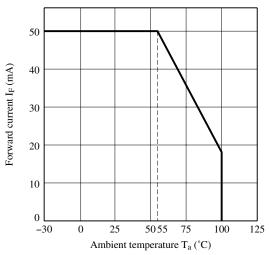


Fig.3 Diode Power Dissipation vs. Ambient **Temperature**

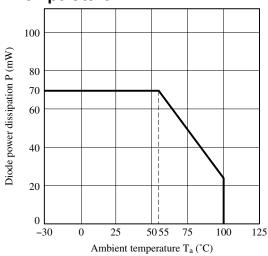


Fig.4 Collector Power Dissipation vs. **Ambient Temperature**

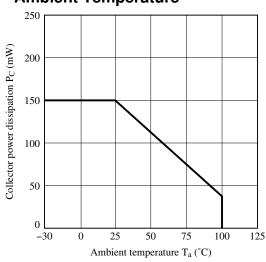
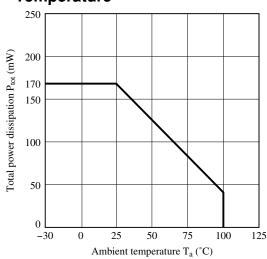


Fig.5 Total Power Dissipation vs. Ambient **Temperature**



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Fig.6 Peak Forward Current vs. Duty Ratio

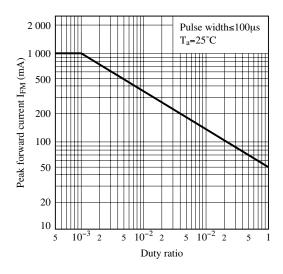


Fig.8 Current Transfer Ratio vs. Forward Current

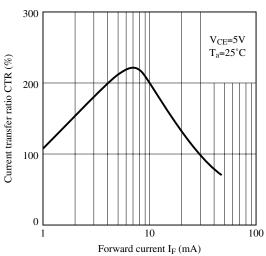


Fig.10 Relative Current Transfer Ratio vs.
Ambient Temperature

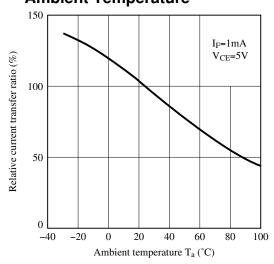


Fig.7 Forward Current vs. Forward Voltage

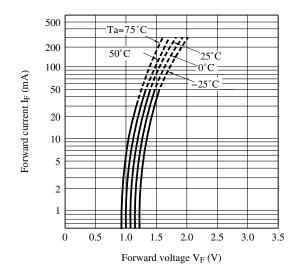


Fig.9 Collector Current vs. Collector-emitter Voltage

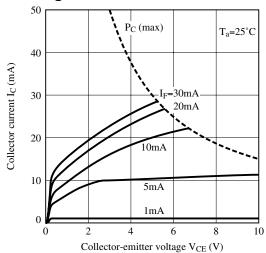


Fig.11 Collector - emitter Saturation Voltage vs. Ambient Temperature

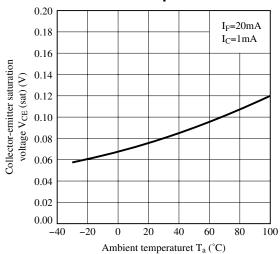




Fig.12 Collector Dark Current vs. Ambient Temperature

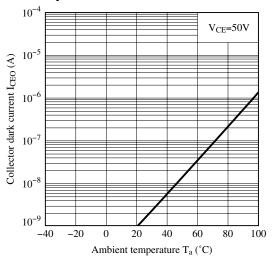
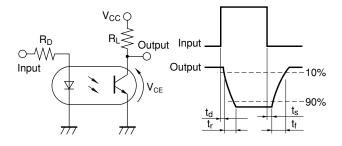


Fig.14 Test Circuit for Response Time



Please refer to the conditions in Fig.13

Fig.16 Collector-emitter Saturation Voltage

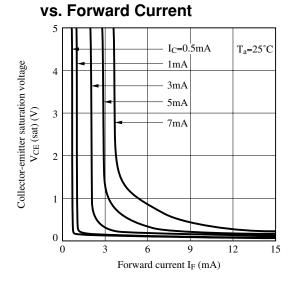


Fig.13 Response Time vs. Load Resistance

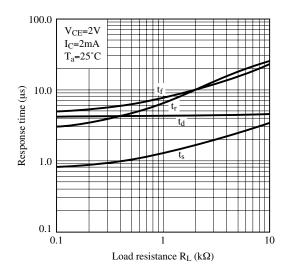
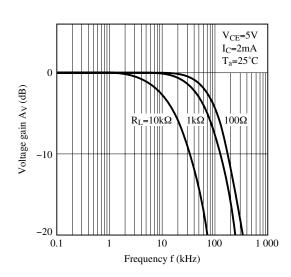


Fig.15 Frequency Response



Remarks: Please be aware that all data in the graph are just for reference and not for guarantee.



■ Design Considerations

Design guide

While operating at I_F<1.0mA, CTR variation may increase.

Please make design considering this fact.

In case that some sudden big noise caused by voltage variation is provided between primary and secondary terminals of photocoupler some current caused by it is floating capacitance may be generated and result in false operation since current may go through IRED or current may change.

If the photocoupler may be used under the circumstances where noise will be generated we recommend to use the bypass capacitors at the both ends of IRED.

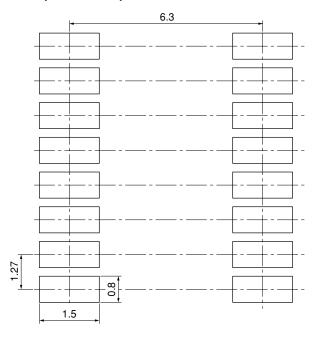
This product is not designed against irradiation and incorporates non-coherent IRED.

Degradation

In general, the emission of the IRED used in photocouplers will degrade over time.

In the case of long term operation, please take the general IRED degradation (50% degradation over 5years) into the design consideration.

Recommended Foot Print (reference)



(Unit: mm)

[☆] For additional design assistance, please review our corresponding Optoelectronic Application Notes.



■ Manufacturing Guidelines

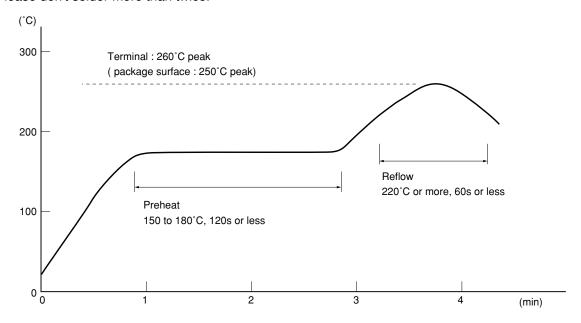
Soldering Method

Reflow Soldering:

Reflow soldering should follow the temperature profile shown below.

Soldering should not exceed the curve of temperature profile and time.

Please don't solder more than twice.



Flow Soldering:

Due to SHARP's double transfer mold construction submersion in flow solder bath is allowed under the below listed guidelines.

Flow soldering should be completed below 260°C and within 10s.

Preheating is within the bounds of 100 to 150°C and 30 to 80s.

Please don't solder more than twice.

Hand soldering

Hand soldering should be completed within 3s when the point of solder iron is below 400°C.

Please don't solder more than twice.

Other notices

Please test the soldering method in actual condition and make sure the soldering works fine, since the impact on the junction between the device and PCB varies depending on the tooling and soldering conditions.



Cleaning instructions

Solvent cleaning:

Solvent temperature should be 45°C or below Immersion time should be 3minutes or less

Ultrasonic cleaning:

The impact on the device varies depending on the size of the cleaning bath, ultrasonic output, cleaning time, size of PCB and mounting method of the device.

Therefore, please make sure the device withstands the ultrasonic cleaning in actual conditions in advance of mass production.

Recommended solvent materials:

Ethyl alcohol, Methyl alcohol and Isopropyl alcohol

In case the other type of solvent materials are intended to be used, please make sure they work fine in actual using conditions since some materials may erode the packaging resin.

Presence of ODC

This product shall not contain the following materials.

And they are not used in the production process for this device.

Regulation substances: CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBBOs and PBBs are not used in this product at all.

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■ Package specification

● Tape and Reel package

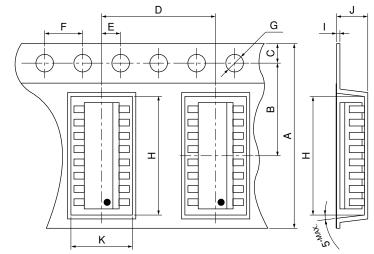
Package materials

Carrier tape : PS

Cover tape: PET (three layer system)

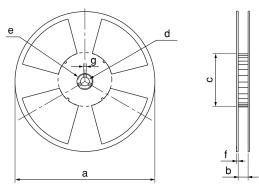
Reel: PS

Carrier tape structure and Dimensions



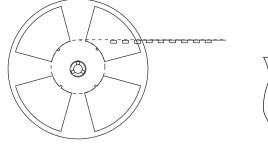
(Unit: mm) Dimensions List F С D Е G 24.0±0.3 11.5^{±0.1} 1.75^{±0.1} 12.0^{±0.1} $2.0^{\pm0.1}$ $4.0^{\pm0.1}$ $\phi 1.5^{+0.1}_{-0}$ Н K $0.4^{\pm0.05}$ $10.8^{\pm0.1}$ $3.0^{\pm0.1}$ $7.4^{\pm0.1}$

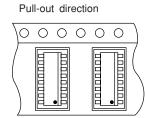
Reel structure and Dimensions



Dimensio	ns List	(Unit: mm)		
a	b	С	d	
330	25.5 ^{±1.5}	100±1.0	13 ^{±0.5}	
e	f	g		
23±1.0	2.0±0.5	$2.0^{\pm0.5}$		

Direction of product insertion





[Packing: 1 000pcs/reel]



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